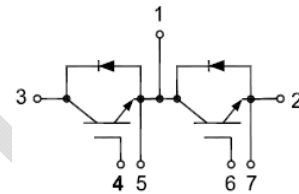
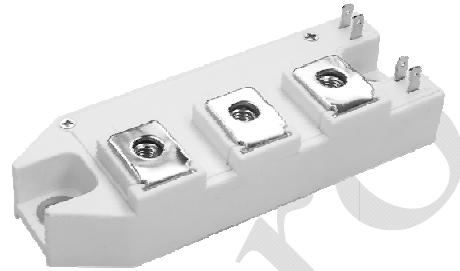


# GF75HF120T1H

## IGBT Module

### Features:

- Short Circuit Rated > 10 $\mu$ s
- Low Saturation Voltage:  $V_{CE(sat)} = 3.30V @ I_C = 75A, T_C = 25^\circ C$
- Low Switching Loss
- 100% RBSOA Tested ( $2 \times I_C$ )
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



### Applications:

- Welding Machine, Cutting Machine
- Plating Power Supply, Induction Heating
- SMPS, UPS

### Maximum Rated Values of IGBT ( $T_C = 25^\circ C$ unless otherwise specified)

$V_{CES}$	Collector-Emitter Blocking Voltage		1200	V
$V_{GES}$	Gate-Emitter Voltage		$\pm 20$	V
$I_C$	Continuous Collector Current	$T_C = 80^\circ C$	75	A
		$T_C = 25^\circ C$	150	A
$I_{CM}$	Repetitive Peak Collector Current	$T_J = 175^\circ C$	150	A
$t_{SC}$	Short Circuit Withstand Time		> 10	$\mu s$
$P_D$	Maximum Power Dissipation per IGBT	$T_C = 25^\circ C$ $T_{Jmax} = 175^\circ C$	610	W

## Electrical Characteristics of IGBT ( $T_C=25^\circ\text{C}$ unless otherwise specified)

### Static Characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 1\text{mA}, V_{CE} = V_{GE}$	4.5	5.0	5.5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 40\text{A}, V_{GE} = 15\text{V}$	$T_J = 25^\circ\text{C}$	3.30	3.50	V
			$T_J = 125^\circ\text{C}$	3.80		V
$I_{CES}$	Collector-Emitter Leakage Current	$V_{GE} = 0\text{V}, V_{CE} = V_{CES}, T_J = 25^\circ\text{C}$			1	mA
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}, T_J = 25^\circ\text{C}$			400	nA
$C_{ies}$	Input Capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		9.5		nF
$C_{oes}$	Output Capacitance			0.70		nF

### Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 600\text{V}, I_C = 75\text{A}, R_G = 15\Omega, V_{GE} = \pm 15\text{V},$ Inductive Load	$T_J = 25^\circ\text{C}$	160		ns
			$T_J = 125^\circ\text{C}$	150		
$t_r$	Rise Time		$T_J = 25^\circ\text{C}$	90		ns
			$T_J = 125^\circ\text{C}$	100		
$t_{d(off)}$	Turn-off Delay Time		$T_J = 25^\circ\text{C}$	440		ns
			$T_J = 125^\circ\text{C}$	470		
$t_f$	Fall Time		$T_J = 25^\circ\text{C}$	120		ns
			$T_J = 125^\circ\text{C}$	160		
$E_{on}$	Turn-on Switching Loss		$T_J = 25^\circ\text{C}$	5.7		mJ
			$T_J = 125^\circ\text{C}$	6.8		
$E_{off}$	Turn-off Switching Loss	$T_J = 25^\circ\text{C}$	1.8		mJ	
		$T_J = 125^\circ\text{C}$	3.2			
$Q_g$	Total Gate Charge	$T_J = 25^\circ\text{C}$	820		nC	
RBSOA	Reverse Bias Safe Operation Area	$I_C=150\text{A}, V_{CC}=1050\text{V}, V_p=1200\text{V}, R_g = 15\Omega, V_{GE}=+15\text{V to } 0\text{V}, T_J = 150^\circ\text{C}$	Trapezoid			
SCSOA	Short Circuit Safe Operation Area	$V_{CC} = 600\text{V}, V_{GE} = 15\text{V}, T_J = 150^\circ\text{C}$	10		$\mu\text{s}$	
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case			0.21	$^\circ\text{C/W}$	

**Maximum Rated Values of Diode ( $T_C=25^{\circ}\text{C}$  unless otherwise specified)**

$V_{RRM}$	Repetitive Peak Reverse Voltage	1200	V
$I_F$	Diode Continuous Forward Current	75	A
$I_{FM}$	Diode Maximum Forward Current	150	A

**Electrical Characteristics of Diode ( $T_C=25^{\circ}\text{C}$  unless otherwise specified)**

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{FM}$	Forward Voltage	$I_F = 75\text{A}$	$T_J = 25^{\circ}\text{C}$	2.20		V
			$T_J = 125^{\circ}\text{C}$		2.40	
$I_{rr}$	Peak Reverse Recovery Current		$T_J = 25^{\circ}\text{C}$	45		A
			$T_J = 125^{\circ}\text{C}$		60	
$Q_{rr}$	Reverse Recovery Charge	$I_F = 75\text{A},$ $di/dt = 850\text{A}/\mu\text{s},$ $V_{rr} = 950\text{V},$ $V_{GE} = -15\text{V}$	$T_J = 25^{\circ}\text{C}$	4.0		$\mu\text{C}$
			$T_J = 125^{\circ}\text{C}$		8.2	
$E_{rec}$	Reverse Recovery Energy		$T_J = 25^{\circ}\text{C}$	1.5		mJ
			$T_J = 125^{\circ}\text{C}$		3.3	
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case				0.49	$^{\circ}\text{C}/\text{W}$

**Module**

Symbol	Description		Min	Typ	Max	Unit
$V_{iso}$	Isolation Voltage (All Terminals Shorted)	$f = 50\text{Hz}, 1\text{minute}$	2500			V
$T_J$	Maximum Junction Temperature				175	$^{\circ}\text{C}$
$T_{JOP}$	Maximum Operating Junction Temperature Range		-40		+150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature		-40		+125	$^{\circ}\text{C}$
CTI	Comparative Tracking Index		200			V
$R_{\theta CS}$	Case-To-Sink Thermally (Conductive Grease Applied)			0.1		$^{\circ}\text{C}/\text{W}$
T	Power Terminals Screw:M5		3.0		5.0	N·m
T	Mounting Screw:M6		4.0		6.0	N·m
G	Weight			133		g

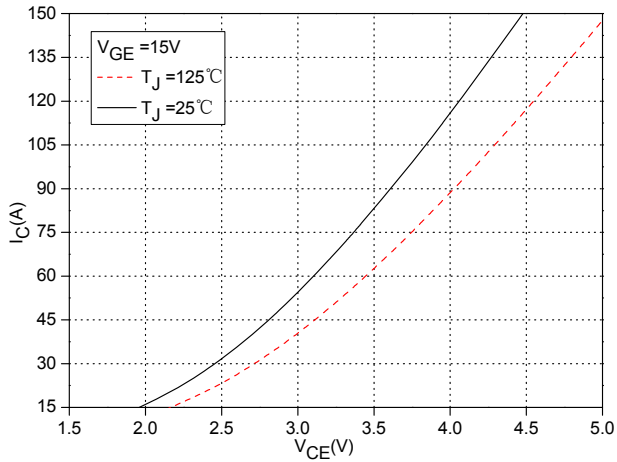


Fig.1 Typical Saturation Voltage Characteristics

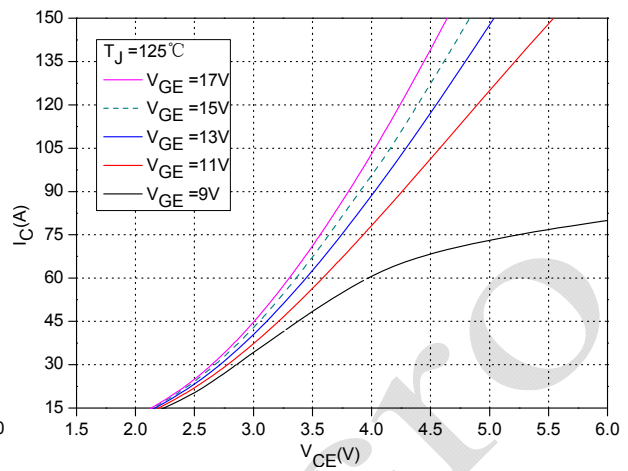


Fig.2 Typical Output Characteristics

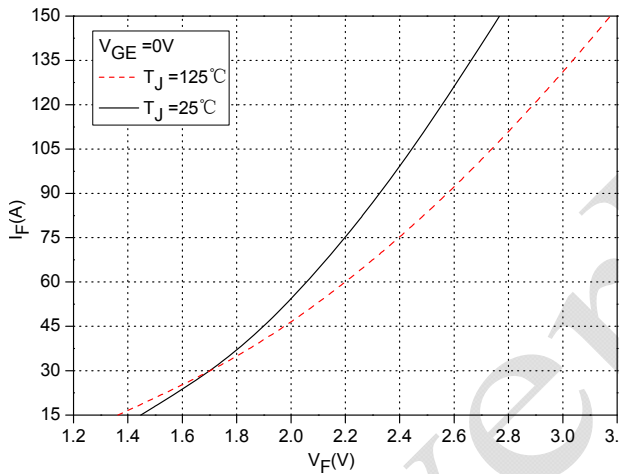


Fig.3 Forward Characteristics of Diode

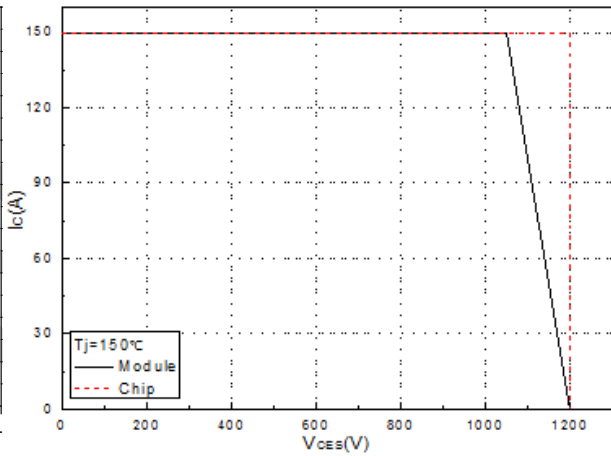


Fig.4 Reverse Bias Safe Operation Area (RBSOA)

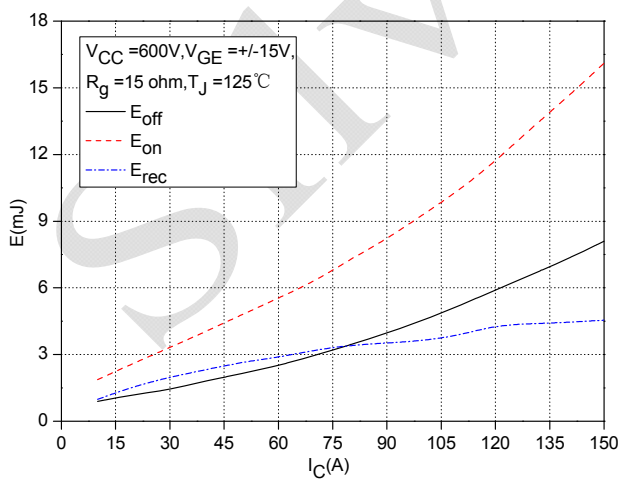


Fig.5 Typical Switching Loss vs. Collector Current

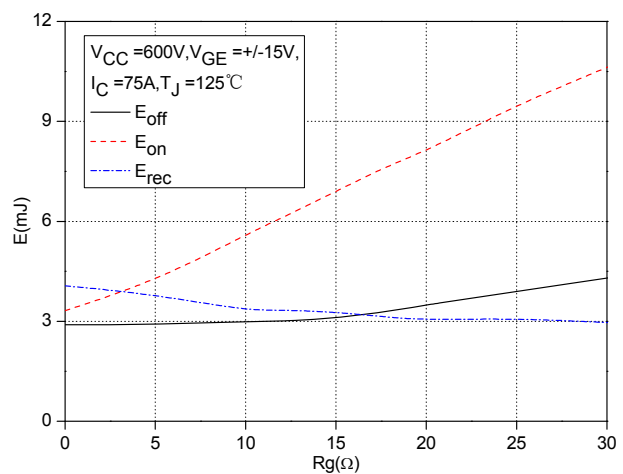


Fig.6 Typical Switching Loss vs. Gate Resistance

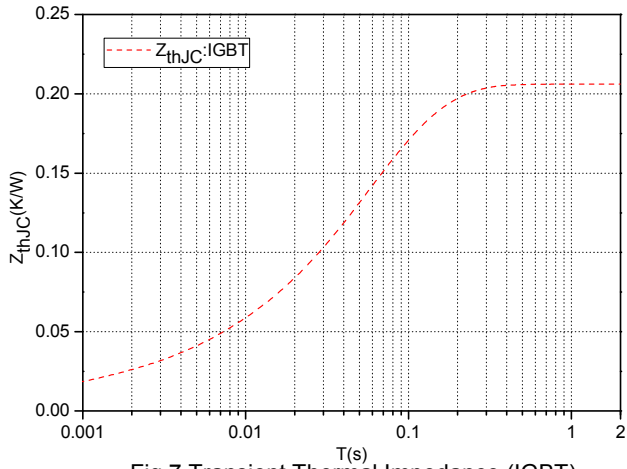


Fig.7 Transient Thermal Impedance (IGBT)

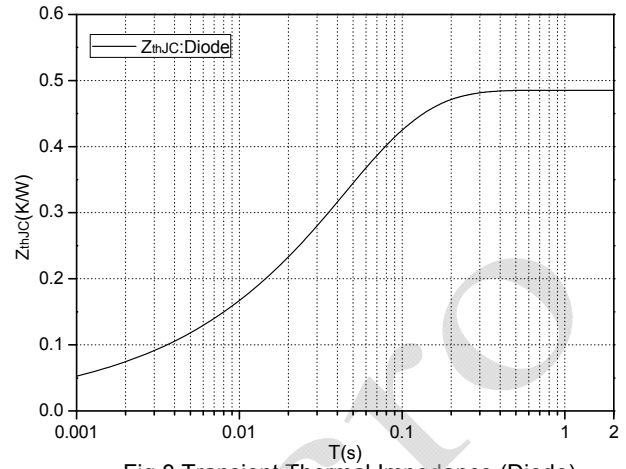


Fig.8 Transient Thermal Impedance (Diode)

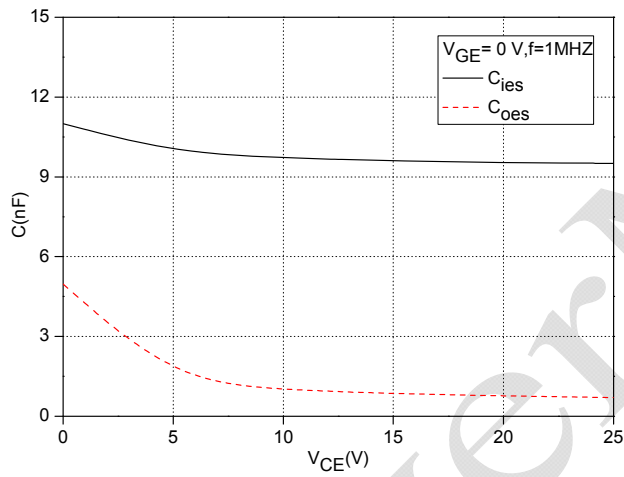
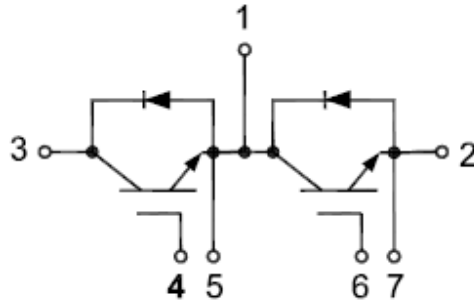
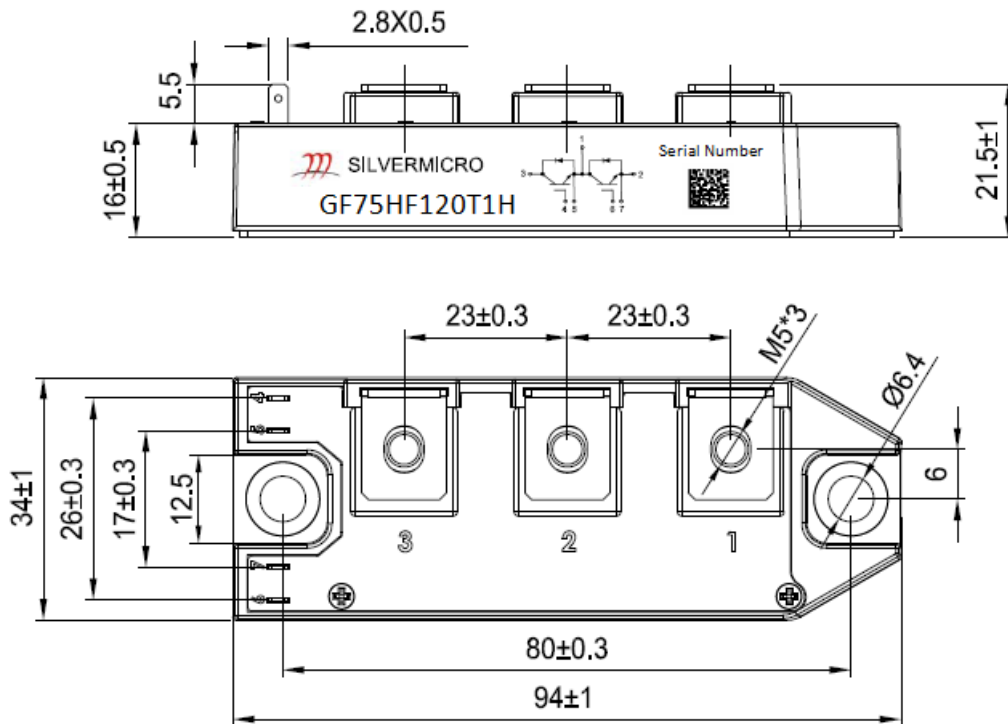


Fig.9 Capacitance Characteristics

**Internal Circuit**



**Package Outline (Unit: mm):**





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